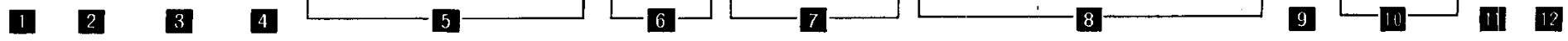


FOR USE BY ELECTRICIANS OVERSEAS :

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (Ta=25°C)					電 氣 的 特 性 (Ta=25°C)										外 形	備 考
				V _{CEO} (V)	V _{ESD} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CEO} 最大値 (μA)	V _{CE} (V)	直 流 又 は パ ル ス h _{FE}		バ イ ア ス		h _{FE}	h _{ie}	h _{ie} *	h _{FE} *		



- 1** TYPE NUMBER
- 2** ORIGINAL MANUFACTURER
- 3** USES
- 4** MATERIAL AND STRUCTURE
- 5** MAXIMUM RATINGS
- 6** I_{CBO} MAXIMUM VALUE AND V_{CE} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7** STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8** STANDARD VALUE OF h PARAMETERS AND BIAS V_{CE}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9** f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T.
- 10** C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11** OUTLINE
- 12** REMARKS

: とコンプリ : COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外 形	備 考			
				V _{CEO} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _j (°C)	I _{CEO} 最大値		直 流 又 は パ ル ス h _{FE}			バ イ ア ス		h _{fe} h _{fb} *	h _{ie} h _{ib} * (Ω)	h _{re} h _{rb} * (×10 ⁻⁴)	h _{oe} h _{ob} * (μU)			f _{ab} f _T * (Mc)	C _{ob} (pF)	r _{bb} h _{ie} (real)* (Ω)
									μA	V _{CB} (V)	V _{CE} (V)	I _C (mA)	V _{CB} (V)	I _E (mA)	NF=2.5dB (f=1MHz, 6V, 0.5mA)									
2SC1004A	東 芝	PA. SW	Si. TMe	1500	5	500	50 W (T _c =25°C)	150	10	500	30~160	15	150	15	-200				5.5*	40	10	102		
★ " 1005	"	PA	"	1100	5	5 A	50 W (T _c =25°C)	150	10	500	12	15	4 A	15	-500				3*	150	5	102		
" 1006	日 電	RF. AF	Si. E	50	5	30	300	150	0.05	30	600	3	1	6	-1		15k	1.5	35	90*	3.5	50*	49C	2SA573 とコンプリ
" 1007	"	RF. SW	"	60	8	20	300	150	0.1	40	150	1	10	10	-10				250*	3.4	30*	49C		
" 1008	"	RF	"	80	8	700	800	150	0.1	60	160	2	50	10	-50				75*	17	25*	84B	2SA708 とコンプリ	
★ " 1009	"	RF. Conv. Mix. Osc. LN	"	50	5	50	150	125	0.1	15	80	3	0.5	6	-1				250*	2	C _c r _{bb} 25pS	176		
" 1010	"	AF. LN	"	50	5	30	300	150	0.05	30	550	3	1	6	-1		15k	1.5	35	90*	3.5	50*	49C	2SA573 とコンプリ
" 1011	三 菱	PA	Si. EP	40	4	750	8.6W (T _c =25°C)	175	100	15	50	10	100			P _o = 3 W (f = 150 MHz, V _{cc} = 15 V, P _i = 250 mW)						271		
" 1012	松 下		Si. TP	165	5	60	2.5 W (T _c =25°C)		2	12	60	20	40	10	-3	35	300	0.4	2.7	100*		C _c r _{bb} 60pS	84B	
★ " 1013	三 菱	SW. P	Si. EP	35	5	1.5 A	7 W (T _c =25°C)	150	1	25	80	4	500			t _{on} < 0.2 μS, t _{off} < 1.2 μS t _s < 1 μS						132		
★ " 1014	"	"	"	50	5	1.5 A	7 W (T _c =25°C)	150	1	25	70	4	500			t _{on} < 0.2 μS, t _{off} < 1.2 μS t _s < 1 μS						132		
★ " 1015	"	PA	"	40	4.5	3 A	33 W (T _c =25°C)	175	500	15	50	10	100			P _o = 14 W (f = 450 MHz, V _{cc} = 13.5 V, P _i = 6 W)						126		
★ " 1016	"	"	"	35		500	2 W	200	50	15	50	10	100			P _o = 1.3 W (f = 500 MHz, V _{cc} = 12 V, P _i = 0.3 mW)						271		
" 1017	"	"	"	75	4	1 A	4 W (T _c =25°C)	125	10	30	50	10	100			P _o = 60 mW (f = 27 MHz, I _C = 25 mA, V _{cc} = 12 V)						132		
★ " 1018	"	"	"	75	4	1 A	4 W (T _c =25°C)	125	10	30	50	10	100			P _o = 1.4 W (f = 27 MHz, P _i = 75 mW, V _{cc} = 12 V)						132		
★ " 1019	"	"	"	60		4 A	40 W (T _c =25°C)	175	1mA	30	50	10	100			P _o = 28 W (f = 500 MHz, V _{cc} = 28 V, P _i = 20 W)						188		
★ " 1020	"	"	"	60		8 A	70 W (T _c =25°C)	175	2mA	30	50	10	100			P _o = 45 W (f = 500 MHz, V _{cc} = 28 V, P _i = 20 W)						188		
★ " 1021	"	"	"	60	5	6 A	60 W (T _c =25°C)	175	2 mA	30	50	10	100			P _o = 45 W (f = 90 MHz, V _{cc} = 28 V, P _i = 5 W)						127		
★ " 1022	"	"	"	60	5	6 A	60 W (T _c =25°C)	175	2 mA	30	50	10	100			P _o = 45 W (f = 150 MHz, V _{cc} = 28 V, P _i = 10 W)						127		
★ " 1023	富 士 通	RF. Conv. Mix. Osc.	Si. P	25	3	25	150	125	2	12	40	6	1	6	-2				200*	1.8		138		
★ " 1024	三 洋	PA	Si. TMe	60	4	3 A	25 W (T _c =25°C)	150	1 mA	55	25~200	2	1 A										99	
" 1025	"	"	"	200	6	3 A	25 W (T _c =25°C)	150	1 mA	180	40~320	2	500	5	-500				8*	100		99		
★ " 1026	富 士 通	RF. Conv.	Si. P	25	3	25	150	125	2	12	70	6	1	6	-2				NF=2.5dB (f=1MHz, 6V, 1mA)			70*	138	
★ " 1027	三 洋	SW	Si. Me	250	5	6 A	50 W (T _c =25°C)	150	1 mA	30	> 9	2	5 A											
" 1028																								
" 1029																								
" 1030	日 立	PA	Si. T	150	6	6 A	50 W (T _c =25°C)	150	1 mA	30	80	5	1 A	5	-1 A				10*	180		102	2SA756 とコンプリ	
" 1031	日 電	SW	Si. TMe	300	6	2 A	30 W (T _c =25°C)	175	5	150	220	10	500	10		t _{on} < 5 μS, t _{off} < 15 μS t _{stg} < 5 μS				15*		99		
★ " 1032	富 士 通	RF	Si. P	25	3	25	150	125	2	12	100	6	1	6	-2				200*	1.8	70*	138		
★ " 1033	松 下	RF. AF	Si. TP	200	5	25	300	175	2	12	> 30	10	5	10	-3	38	300	0.4	2.9	135*	3.3	C _c r _{bb} 60pS	49C	